### 2N6040 2N6041 2N6042 PNP 2N6043 2N6044 2N6045 NPN

# COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

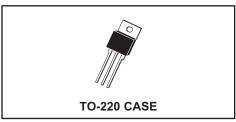


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## **DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N6040 and 2N6043 Series types are Complementary Silicon Power Transistors, manufactured by the epitaxial base process, designed for general purpose amplifier applications.

### MARKING: FULL PART NUMBER



MAXIMUM RAT	FINGS: (T <sub>C</sub> =25°C)	SYMBOL V <sub>CBO</sub>	2N6040 2N6043 60	<b>2N6041</b> <b>2N6044</b> 80	2N6042 2N6045 100	UNITS V
	· ·	020				V
Collector-Emitte	i voltage	V <sub>CEO</sub>	60	80	100	•
Emitter-Base Voltage		$V_{EBO}$		5.0		V
Continuous Collector Current		I <sub>C</sub>		8.0		Α
Peak Collector	Current	I <sub>CM</sub>		16		Α
Base Current		Ι <sub>Β</sub>		120		mA
Power Dissipation		$P_{D}$		75		W
Operating and Storage Junction Temperature		T <sub>J</sub> , T <sub>stg</sub>		-65 to +150		°C
Thermal Resista	ance	$\Theta$ JC		1.67		°C/W
ELECTRICAL (	CHARACTERISTICS: (T <sub>C</sub> =25°C	unless otherw	ise noted)			
SYMBOL	TEST CONDITIONS		,	MIN	MAX	UNITS
I <sub>CBO</sub>	V <sub>CB</sub> =Rated V <sub>CBO</sub>				20	μΑ
I <sub>CEV</sub>	V <sub>CE</sub> =Rated V <sub>CEO</sub> , V <sub>BE(OFF)</sub> =1.5V			20	μΑ	
ICEV V <sub>CE</sub> =Rated V <sub>CEO</sub> , V <sub>BE(OFF)</sub> =1.5V, T <sub>C</sub> =150°C			200	μΑ		

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I <sub>CBO</sub>	V <sub>CB</sub> =Rated V <sub>CBO</sub>		20	μΑ
I <sub>CEV</sub>	V <sub>CE</sub> =Rated V <sub>CEO</sub> , V <sub>BE(OFF)</sub> =1.5V		20	μΑ
ICEV	V <sub>CE</sub> =Rated V <sub>CEO</sub> , V <sub>BE(OFF)</sub> =1.5V, T <sub>C</sub> =150°C		200	μΑ
ICEO	V <sub>CE</sub> =Rated V <sub>CEO</sub>		20	μΑ
I <sub>EBO</sub>	V <sub>EB</sub> =5.0V		2.0	mA
BVCEO	I <sub>C</sub> =100mA (2N6040, 2N6043)	60		V
BVCEO	I <sub>C</sub> =100mA (2N6041, 2N6044)	80		V
<b>BV</b> CEO	I <sub>C</sub> =100mA (2N6042, 2N6045)	100		V
V <sub>CE</sub> (SAT)	I <sub>C</sub> =4.0A, I <sub>B</sub> =16mA (2N6040, 2N6041, 2N6043, 2N6044)		2.0	V
V <sub>CE</sub> (SAT)	I <sub>C</sub> =3.0A, I <sub>B</sub> =12mA (2N6042, 2N6045)		2.0	V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =8.0A, I <sub>B</sub> =80mA		4.0	V
V <sub>BE(SAT)</sub>	I <sub>C</sub> =8.0A, I <sub>B</sub> =80mA		4.5	V
V <sub>BE(ON)</sub>	$V_{CE}$ =4.0V, $I_{C}$ =4.0A		2.8	V
h <sub>FE</sub>	V <sub>CE</sub> =4.0V, I <sub>C</sub> =4.0A (2N6040, 2N6041, 2N6043, 2N6044)	1,000	20,000	
hFE	V <sub>CE</sub> =4.0V, I <sub>C</sub> =3.0A (2N6042, 2N6045)	1,000	20,000	
h <sub>FE</sub>	$V_{CE}$ =4.0V, $I_{C}$ =8.0A	100		

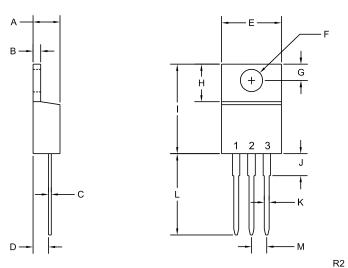
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# COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

ELECTRIC	AL CHARACTERISTICS - Continued: ( $ op$	=25°C unless o	therwise noted)	
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h <sub>fe</sub>	$V_{CE}$ =4.0V, $I_{C}$ =3.0A, f=1.0kHz	300		
$f_{T}$	$V_{CE}$ =4.0V, $I_{C}$ =3.0A, f=1.0MHz	4.0		MHz
C <sub>ob</sub>	$V_{CB}$ =10V, $I_E$ =0, f=100kHz (NPN Types)		200	pF
C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=100kHz (PNP Types)		300	pF

#### **TO-220 CASE - MECHANICAL OUTLINE**



	DIMENSIONS				
	INCHES		MILLIMETERS		
SYMBOL	MIN	MAX	MIN	MAX	
Α	0.170	0.190	4.31	4.82	
В	0.045	0.055	1.15	1.39	
С	0.013	0.026	0.33	0.65	
D	0.083	0.107	2.10	2.72	
E	0.394	0.417	10.01	10.60	
F (DIA)	0.140	0.157	3.55	4.00	
G	0.100	0.118	2.54	3.00	
Н	0.230	0.270	5.85	6.85	
	0.560	0.625	14.23	15.87	
J	-	0.250	-	6.35	
K	0.025	0.038	0.64	0.96	
L	0.500	0.579	12.70	14.70	
М	0.090	0.110	2.29	2.79	
TO-220 (REV: R2)					

## LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR

MARKING:

**FULL PART NUMBER** 

R1 (16-November 2009)

#### **OUTSTANDING SUPPORT AND SUPERIOR SERVICES**



#### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- · Inventory bonding
- · Consolidated shipping options

- · Custom bar coding for shipments
- · Custom product packing

#### **DESIGNER SUPPORT/SERVICES**

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- · Custom electrical curves
- · Environmental regulation compliance
- · Customer specific screening
- · Up-screening capabilities

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- Custom product and package development

#### REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

#### **CONTACT US**

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